

ESJG150N03A

Rev-1.2

SuperMOS - PDFN5*6-8L 30V BV_{DSS} , $1.7m\Omega$ $R_{DS(on)}$, N-channel MOSFET

1. Description

The ESJG150N03A is N-channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESJG150N03A is Pb-free.

2. Features

- 30V, $R_{DS(on)}=1.7m\Omega$ (Typ.) @ $V_{GS}=10V$
 $R_{DS(on)}=2.6m\Omega$ (Typ.) @ $V_{GS}=4.5V$
- Fast Switching
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

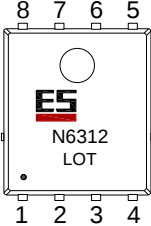
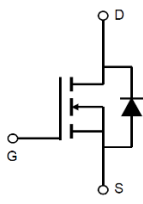
- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel size
ESJG150N03A	PDFN5*6-8L	N6312/LOT	Halogen free	Tape & Reel	5,000 PCS	UL 94V-0	13 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
4	Gate		
1/2/3	Source		
5/6/7/8	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C=25^{\circ}\text{C}$	I_D	123	A
	$T_C=75^{\circ}\text{C}$		95	
Maximum Power Dissipation	$T_C=25^{\circ}\text{C}$	P_D	50	W
	$T_C=75^{\circ}\text{C}$		30	
Pulsed Drain Current		I_{DM}	260	A
Avalanche Current, Single Pulsed ^a		I_{AS}	38	A
Avalanche Energy, Single Pulsed ^a		E_{AS}	216	mJ
Operating Junction Temperature		T_J	150	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 to +150	$^{\circ}\text{C}$

Thermal resistance ratings

Single Operation				
Parameter		Symbol	Max	Unit
Junction-to-Case Thermal Resistance	$t \leq 10 \text{ s}$	$R_{\theta JC}$	2.5	$^{\circ}\text{C/W}$

Note:

a: $T_J=25^{\circ}\text{C}$, $V_{DD}=30\text{V}$, $V_G=10\text{V}$, $L=0.3\text{mH}$, $R_g=25\Omega$

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} =0V, V _{DS} =30V			1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.1	1.75	2.2	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		1.7	2.2	mΩ
		V _{GS} =4.5V, I _D =20A		2.6	3.6	
CHARGES AND CAPACITANCES						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =15V f=1MHz		3100		pF
Output Capacitance	C _{OSS}			882		
Reverse Transfer Capacitance	C _{RSS}			103		
Total Gate Charge	Q _{G(TOT)}	V _{GS} =10V, V _{DS} =15V I _D =20A		43		nC
Gate-to-Source Charge	Q _{GS}			8.5		
Gate-to-Drain Charge	Q _{GD}			6		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =10V, V _{DD} =15V, R _G =3Ω, R _L =0.75Ω		11.5		ns
Rise Time	t _r			5.2		
Turn-Off Delay Time	t _{d(OFF)}			40		
Fall Time	t _f			8		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _{SD} =20A			1.5	V

7. Typical Characteristic

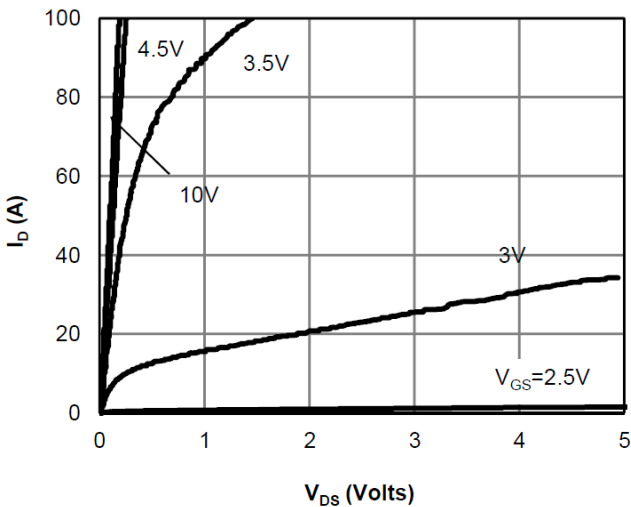


Figure 1: On-Region Characteristics

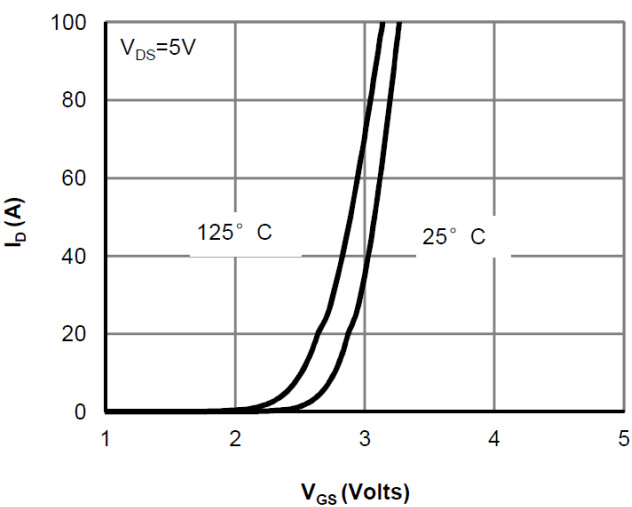


Figure 2: Transfer Characteristics

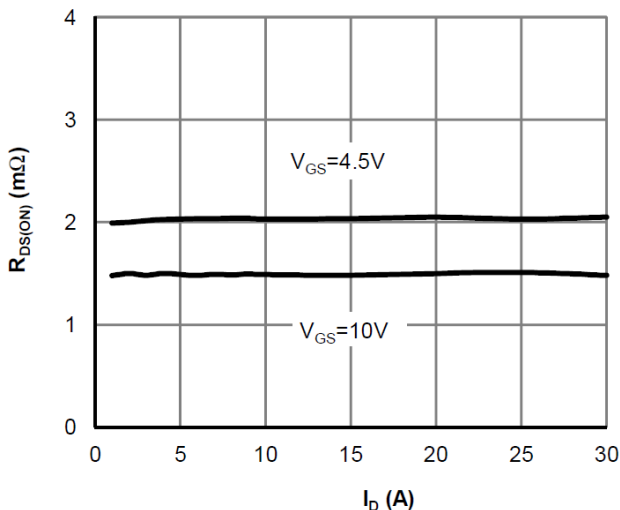


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

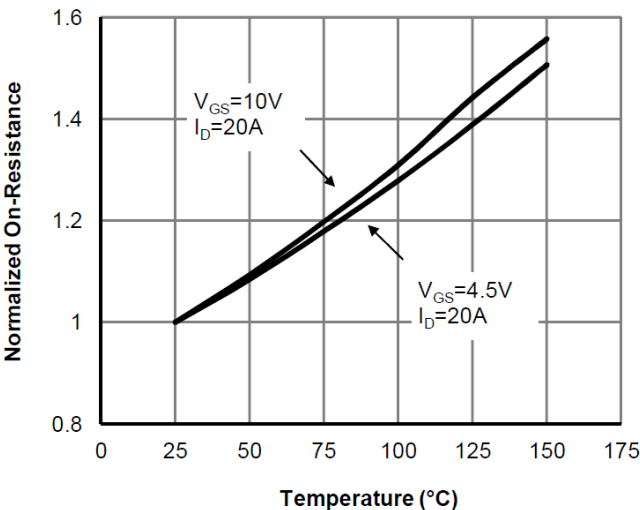


Figure 4: On-Resistance vs. Junction Temperature

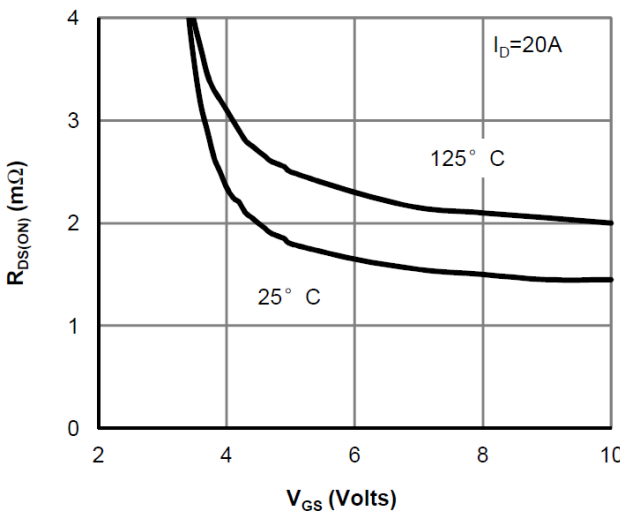


Figure 5: On-Resistance vs. Gate-Source Voltage

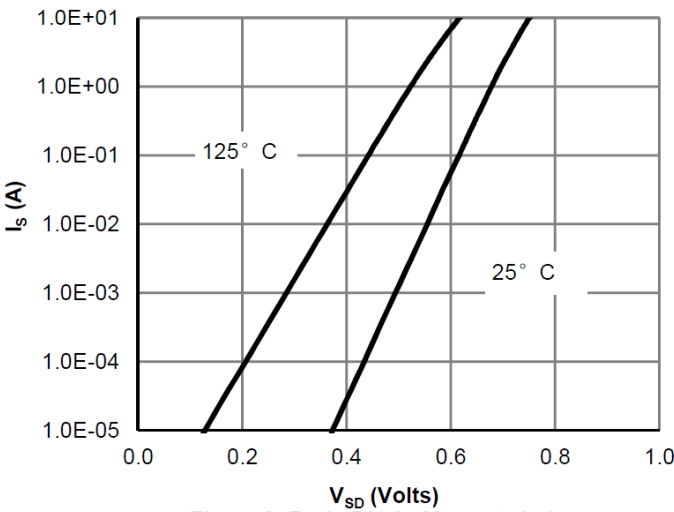
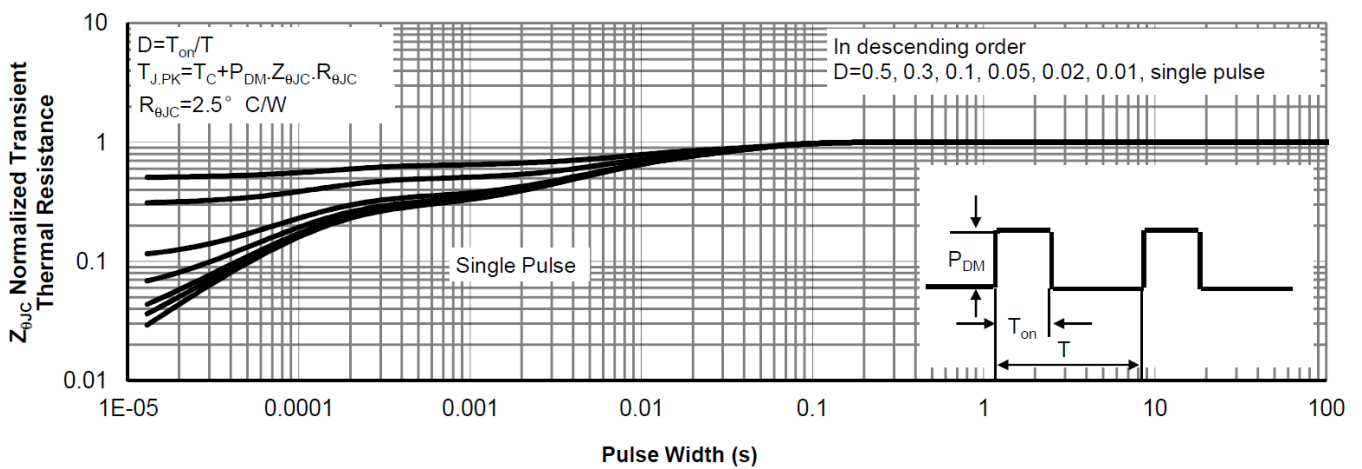
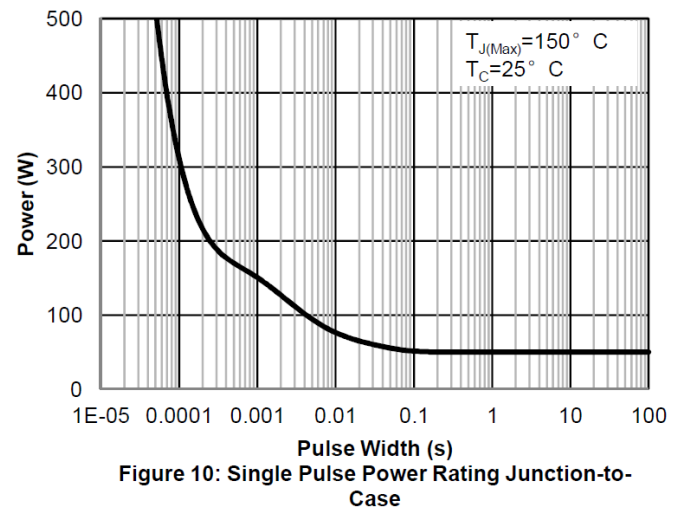
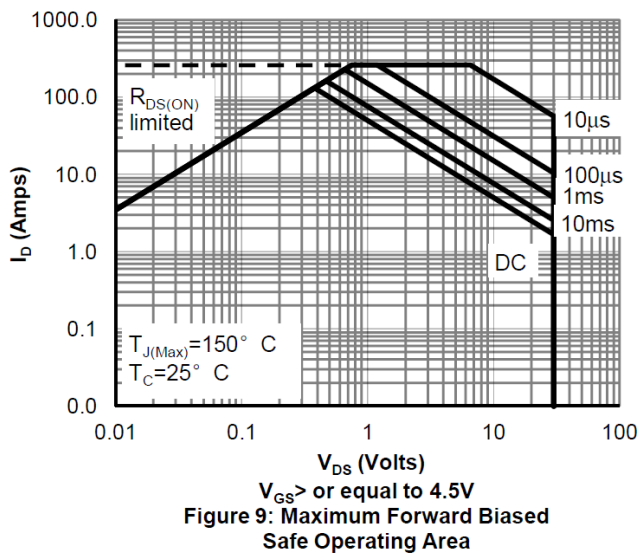
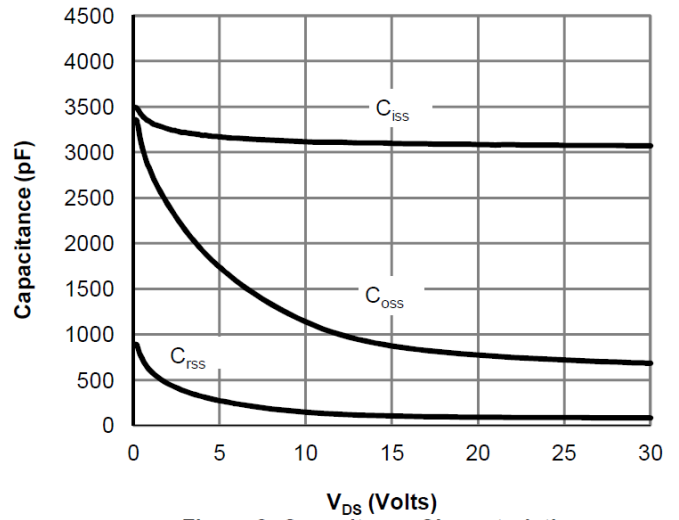
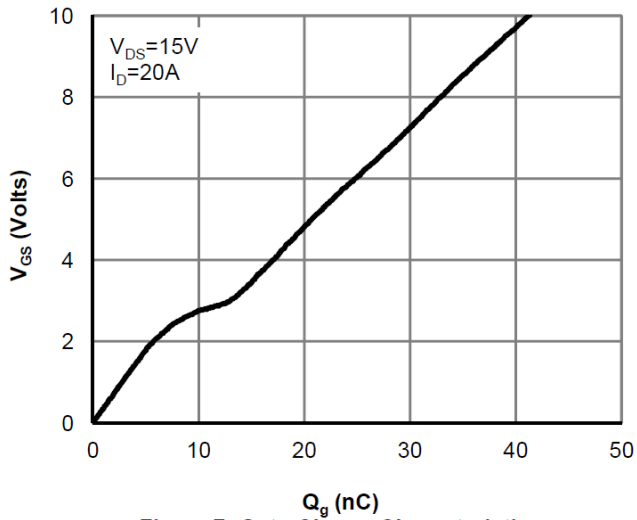
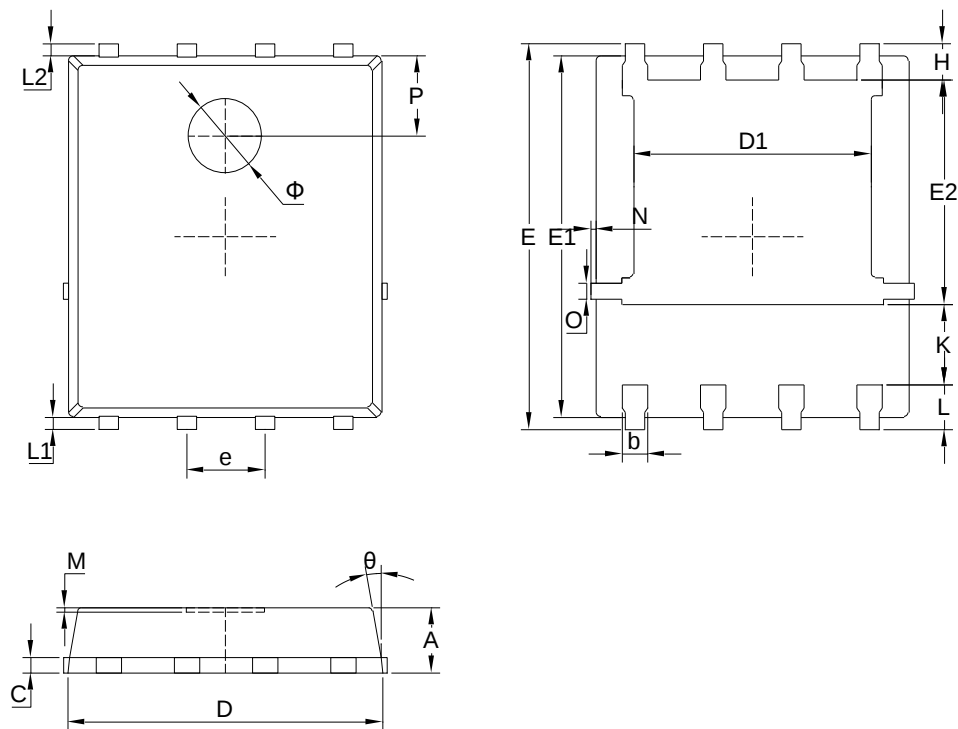


Figure 6: Body-Diode Characteristics



8. Dimension (PDFN5*6-8L)



Symbol	Dimensions in Millimeters			Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX		MIN	NOM	MAX
A	0.90	1.05	1.20	H	0.48	0.58	0.68
b	0.35	0.40	0.50	K	1.17	1.27	1.37
C	0.20	0.25	0.35	L	0.64	0.74	0.84
D	4.90	5.05	5.20	L1/L2	0.20 REF.		
D1	3.72	3.82	3.92	θ	8°	10°	12°
E	6.00	6.15	6.30	M	0.08 REF.		
E1	5.60	5.75	5.90	N	0	-	0.15
E2	3.47	3.57	3.67	O	0.25 REF.		
e	1.27 BSC.			P	1.28 REF.		
Φ	1.20 REF						

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